

ABSTRACT OF THE DISCLOSURE

SEMICONDUCTOR LASER AND A MANUFACTURING METHOD FOR
THE SAME

A semiconductor laser, includes: a first cladding layer; an active layer that is formed on top of the first cladding layer; a second cladding layer that is formed on top of the active layer and has a different type of conductivity to the first cladding layer; an etch-stop layer that is formed on top of the second cladding layer and has a same type of conductivity as the second cladding layer; and a light-confining construction that is formed on top of the etch-stop layer by an etching process. The etch-stop layer has a surface part that contacts the light-confining construction. This surface part is composed of an $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ semiconductor, where $0.2 \leq x < 0.7$ and $0 < y \leq 1$.

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